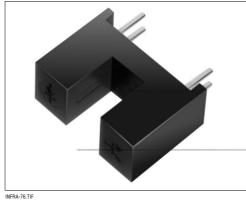
Transmissive Sensor

FEATURES

- Choice of phototransistor or photodarlington output
- · Ambient light and dust protective filter
- 0.200 in.(5.08 mm) slot width



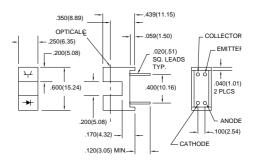
DESCRIPTION

The HOA1886 series consists of an infrared emitting diode facing an NPN silicon phototransistor (HOA1886-011, -012) or photodarlington (HOA1886-013) encased in a black thermoplastic housing with IR transmissive inserts which form the optical windows. This arrangement provides excellent protection against ambient light while eliminating aperture openings which could be clogged by airborne contaminants. Detector switching takes place whenever an opaque object passes through the slot between emitter and detector. The HOA1886 series employs plastic molded components and has a 0.050 in.(1.27 mm) x 0.060 in.(1.52 mm) vertical aperture in front of the detector. For additional component information see SEP8506/8706, SDP8406, and SDP8106.

Housing material is polycarbonate. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals ±0.010(0.25) 2 plc decimals ±0.020(0.51)



DIM_056.ds4



Transmissive Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	I _R			10	μΑ	V _R =3 V
DETECTOR Collector-Emitter Breakdown Voltage HOA1886-011, -012 HOA1886-013	V _(BR) ceo	30 15			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector Dark Current HOA1886-011, -012 HOA1886-013	ICEO			100 250	nA	V _{CE} =10 V I _F =0
COUPLED CHARACTERISTICS On-State Collector Current HOA1886-011 HOA1886-012 HOA1886-013	Ic(on)	0.3 1.8 4.0			mA	V _{CE} =5 V I _F =20 mA
Collector-Emitter Saturation Voltage HOA1886-011 HOA1886-012 HOA1886-013	Vce(sat)			0.4 0.4 1.1	V	I _F =20 mA I _C =40 μA I _C =230 μA I _C =500 μA
Rise And Fall Time HOA1886-011, -012 HOA1886-013	t _r , t _f		15 75		μs	Vcc=5 V, lc=1 mA R_L =1000 Ω R_L =100 Ω

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40°C to 85°C
Storage Temperature Range -40°C to 85°C
Soldering Temperature (5 sec) 240°C
IR EMITTER
Power Dissipation 100 mW (1)
Reverse Voltage 3 V

Continuous Forward Current 50 mA **DETECTOR**Collector-Emitter Voltage 30 V

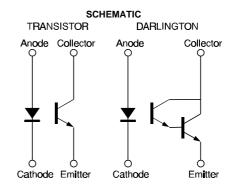
Emitter-Collector Voltage 5 V

Power Dissipation 100 mW (1)

Power Dissipation

Notes

1. Derate linearly at 0.78 mW/°C above 25°C.

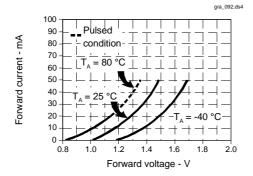


Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

Honeywell

Transmissive Sensor

IRED Forward Bias Characteristics



Non-Saturated Switching Time vs Load Resistance 1000 ▤◾▦▦ Response time - µs 100 Photodarlington = = = = Phototransistor ŦI#I#

100

Collector Current vs

1000

Load resistance - Ohms

10000

75

100

10

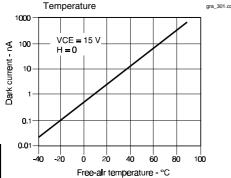
0.2

0.0

-50

Fig. 4

Dark Current vs Fig. 3



Ambient Temperature gra_095.ds4 Normalized collector current 1.0 0.6 0.4

Ó

25

Free-air temperature - °C

50

All Performance Curves Show Typical Values

Transmissive Sensor



Honeywell

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